

U.S. Department of Commerce, Patent and Trademark				Atty. Docket No.		Application No.	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT				SNDK.352US0		10/799,060	
				Applicant(s)			
(Use several sheets if necessary)				Filing Date		Group	
JAN 24 2005				March 12, 2004		2818	
U.S. Patent Documents							
*Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate	
MA	001	5,043,940	8/1991	Harari			
	002	5,070,032	12/1991	Yuan			
	003	5,070,032	12/3/1991	Yuan et al.			
	004	5,095,344	3/1992	Harari			
	005	5,168,465	12/1992	Harari			
	006	5,172,338	12/1992	Mehrotra			
	007	5,198,380	3/1993	Harari			
	008	5,268,318	12/1993	Harari			
	009	5,268,319	12/1993	Harari			
	010	5,297,148	Mar. 22, 1994	Harari et al.			
	011	5,313,421	5/1994	Guterman			
	012	5,315,541	May 24, 1994	Harari et al.			
	013	5,343,063	8/1994	Yuan			
	014	5,343,063	8/30/1994	Yuan et al.			
	015	5,380,672	1/1995	Yuan			
	016	5,512,505	4/1996	Yuan			
	017	5,534,456	7/1996	Yuan			
	018	5,554,553	9/1996	Yuan			
	019	5,579,259	11/1996	Samachisa			
	020	5,595,924	1/1997	Yuan			
	021	5,640,032	Jun. 17, 1997	Tomioka			
	022	5,640,032	6/17/1997	Yugo Tomioka, Tokyo			
	023	5,654,217	8/1997	Yuan			
	024	5,661,053	8/1997	Yuan			
	025	5,677,872	10/1997	Samachisa			
Examiner	Date Considered			08/11/05			
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(Use several sheets if necessary)				Jeffrey Lutze et al.			
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U.S. Published Patent Application Documents							
*Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
UH		055 2001/001491	05/24/2001	Sakui			
		056 2004/0084713	05/2004	Hsieh, Chia-Ta			
		057 2004/0033663	02/2004	Chuang et al.			
		058 2002/0093073	7/18/2002	Mori et al.			
		059 2004/0070021	4/15/2004	Yuan, Jack H.			
		060 2001/0015454	Aug. 23, 2001	Lee Seong-Soo et al.			
Foreign Patent Documents							
						Translation	
		Document	Date	Country	Class	Subclass	Yes No
UH		061 DE 196 17 632	July 3, 1997	Germany			Abstract
OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)							
UH	062	Aritome, Seiichi, "Advanced Flash Memory Technology and Trends for File Storage Application," IEDM Technical Digest, International Electronic Devices Meeting, IEEE, San Francisco, California, December 10-13, 2000, pp 33.1.1-33.1.4.					
	063	Chan, et al., "A True Single-Transistor Oxide-Nitride-Oxide EEPROM Device," IEEE Electron Device Letters, Vol. EDL-8, No. 3, March 1987, pp. 93-95.					
	064	DiMaria et al., "Electrically-alterable read-only-memory using Si-rich SiO ₂ injectors and a floating polycrystalline silicon storage layer," J. Appl. Phys. 52(7), July 1981, pp. 4825-4842.					
	065	Eitan et al., "NROM: A Novel Localized Trapping, 2-Bit Nonvolatile Memory Cell," IEEE Electron Device Letters, Vol. 21, No. 11, November 2000, pp. 543-545.					
	066	Hori et al., "A MOSFET with Si-implanted Gate-SiO ₂ Insulator for Nonvolatile Memory Applications," IEDM 92, April 1992, pp. 469-472.					
	067	Lee, Jae-Duk, et al., "Effects of Parasitic Capacitance on NAND Flash Memory Cell Operation," Non-Volatile Semiconductor Memory Workshop, IEEE, Monterey, California, August 12-16, 2001, pp. 90-92.					
Examiner	[Signature]		Date Considered 08/11/05				
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(Form PTO-1449)		Jeffrey W. LUTZE et al.		6740	
1 of 2		Filing Date		Art Group	
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U.S. Patent Documents							
*Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
De	1	5,554,553	09-1996	Harari	/	/	/
	2	5,716,863	02-1998	Arai	/	/	/
	3	5,817,580	10-1998	Violette	/	/	/
	4	5,966,618	10-1999	Sun et al.	/	/	/
	5	6,184,093 B1	02-2001	Sung	/	/	/
	6	6,326,263 B1	12-2001	Hsieh	/	/	/
	7	6,365,525 B2	04-2002	Miller	/	/	/
	8	6,391,722 B1	05-2002	Koh	/	/	/
	9	6,417,051 B1	07-2002	Takebuchi	/	/	/
	10	6,461,973	10-2002	Hui et al.	/	/	/
	11	6,465,323 B1	10-2002	Yu et al.	/	/	/
	12	6,529,410	03-2003	Han et al.	/	/	/
	13	6,544,431	07-2002	Gill et al.	/	/	/
	14	6,548,374	04-2003	Chung	/	/	/
	15	6,562,682	05-2003	Chiu et al.	/	/	/
	16	6,614,684 B1	09-2003	Shukuri et al.	/	/	/
	17	6,620,681 B1	09-2003	Kim et al.	/	/	/
	18	6,768,161 B2	07-2004	Kinoshita	/	/	/
	19	6,770,932 B2	08-2004	Himeno et al.	/	/	/
	20	6,794,708 B2	09-2004	Mori	/	/	/
	21	6,838,357 B2	01-2005	Chen et al.	/	/	/
	22	6,844,586 B2	01-2005	Ding	/	/	/
De	23	6,894,930	05-2005	Chien et al.	/	/	/
	24	6,898,121	05-2005	Chien et al.	/	/	/

Examiner	De	Date Considered	6/2006
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U.S. Patent Documents							
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U.S. Published Patent Application Documents							
*Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
Dle	25	2002/0048897 A1	04-2002	Hong			
	26	2002/0072197 A1	06-2002	Kang et al.			
	27	2003/0015497 A1	01-2003	Gill et al.			
	28	2003/0029839 A1	02-2003	Chou			
	29	2004/0126972 A1	07-2004	Dong et al.			
Dh	30	2005/0199939 A1	09-2005	Lutze et al.			

Foreign Patent Documents								
							Translation	
		Document	Date	Country	Class	Subclass	Yes	No

OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)		
Dle	31	Park et al., "8Gb MLC (Multi-Level Cell) NAND Flash Memory Using 63 nm Process Technology", Samsung Electronics Co., Ltd., Semiconductor R & D Center, pp. 1-4.

Examiner	Dle	Date Considered	6/2006
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U.S. Patent Documents							
*Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
Dle	1	6,172,395	01/2001	Chen et al.			
	2	6,794,708	09/2004	Mori			
	3	6,897,524	05/2005	Kamiya			
	4	6,891,246	05/2005	Aritome			
Dle	5	7,023,049	04/2006	Takebuchi et al.			

U.S. Published Patent Application Documents							
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Dle	6	2002/197800	12/2002	Hashimoto et al.			

Foreign Patent Documents								
							Translation	
		Document	Date	Country	Class	Subclass	Yes	No
Dle	7	EP 1274132	01/2003	EPO			X	
	8	EP 1363324	11/2003	EPO			X	

OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)		
Dle	9	"Planarized NVRAM Cell with Self-Aligned BL-BL and WL-BL Isolations", IBM Technical Disclosure Bulletin, IBM Corp. New York, US, Vol. 36, No. 2, 1 February 1993, pp. 375-377.

Examiner	Dle	Date Considered	6/2006
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